Complementary Power Darlingtons

For Isolated Package Applications

Designed for general-purpose amplifiers and switching applications, where the mounting surface of the device is required to be electrically isolated from the heatsink or chassis.

Features

- Electrically Similar to the Popular TIP122 and TIP127
- 100 V_{CEO(sus)}
- 5.0 A Rated Collector Current
- No Isolating Washers Required
- Reduced System Cost
- High DC Current Gain -2000 (Min) @ $I_C = 3$ Adc
- UL Recognized, File #E69369, to 3500 V_{RMS} Isolation
- Pb-Free Packages are Available*

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit | |
|---|-----------------------------------|----------------------|------------------|--|
| Collector-Emitter Voltage | V_{CEO} | 100 | Vdc | |
| Collector-Base Voltage | V _{CB} | 100 | Vdc | |
| Emitter-Base Voltage | V _{EB} | 5 | Vdc | |
| RMS Isolation Voltage (Note 1) Test No. 1 Per Figure 14 (for 1 sec, R.H. < 30%, Test No. 2 Per Figure 15 T _A = 25°C) Test No. 3 Per Figure 16 | V _{ISOL} | 4500 3500 1500 | V _{RMS} | |
| Collector Current – Continuous Peak | Ic | 5 8 | Adc | |
| Base Current | Ι _Β | 0.12 | Adc | |
| Total Power Dissipation (Note 2) @ T _C = 25°C Derate above 25°C | P _D | 30 0.24 | W W/°C | |
| Total Power Dissipation @ T _A = 25°C Derate above 25°C | P _D | 2 0.016 | W W/°C | |
| Operating and Storage Junction Temperature Range | T _J , T _{stg} | -65 to +150 | I _C | |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|---|-----------------|------|------|
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ | 62.5 | °C/W |
| Thermal Resistance, Junction-to-Case (Note 2) | $R_{\theta JC}$ | 4.1 | °C/W |
| Lead Temperature for Soldering Purpose | TL | 260 | °C |

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Proper strike and creepage distance must be provided.

 Measurement made with thermocouple contacting the bottom insulated mounting surface (in a location beneath the die), the device mounted on a heatsink with thermal grease and a mounting torque of ≥ 6 in. lbs.



ON Semiconductor®

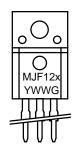
http://onsemi.com

COMPLEMENTARY SILICON POWER DARLINGTONS 5.0 A, 100 V, 30 W

MARKING DIAGRAM



TO-220 CASE 221D-02 STYLE 2



x = 2 or 7
 Y = Year
 WW = Work Week
 G = Pb-Free Package

ORDERING INFORMATION

| Device | Package | Shipping [†] |
|---------|---------------------|-----------------------|
| MJF122 | TO-220 | 50 Units / Rail |
| MJF122G | TO-220 (Pb-Free) | 50 Units / Rail |
| MJF127 | TO-220 | 50 Units / Rail |
| MJF127G | TO-220 (Pb-Free) | 50 Units / Rail |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

| Characteristic | Symbol | Min | Max | Unit | |
|--|----------------------|-----------------------|--------------|------------|------|
| OFF CHARACTERISTICS | | | • | • | • |
| Collector–Emitter Sustaining Voltage (Note 3) $(I_C = 100 \text{ mAdc}, I_B = 0)$ | | V _{CEO(sus)} | 100 | - | Vdc |
| Collector Cutoff Current (V _{CE} = 50 Vdc, I _B = 0) | I _{CEO} | - | 10 | μAdc | |
| Collector Cutoff Current (V _{CB} = 100 Vdc, I _E = 0) | | I _{CBO} | - | 10 | μAdc |
| Emitter Cutoff Current (V _{BE} = 5 Vdc, I _C = 0) | | I _{EBO} | _ | 2 | mAdc |
| ON CHARACTERISTICS (Note 3) | | | • | | • |
| DC Current Gain ($I_C = 0.5$ Adc, $V_{CE} = 3$ Vdc) ($I_C = 3$ Adc, $V_{CE} = 3$ Vdc) | | h _{FE} | 1000 2000 | | _ |
| Collector–Emitter Saturation Voltage ($I_C = 3$ Adc, $I_B = 12$ mAdc) ($I_C = 5$ Adc, $I_B = 20$ mAdc) | V _{CE(sat)} | _ _ | 2 3.5 | Vdc | |
| Base–Emitter On Voltage (I _C = 3 Adc, V _{CE} = 3 Vdc) | V _{BE(on)} | - | 2.5 | Vdc | |
| DYNAMIC CHARACTERISTICS | | | | • | |
| Small-Signal Current Gain (I _C = 3 Adc, V _{CE} = 4 Vdc, f = 1 MHz) | | h _{fe} | 4 | _ | _ |
| Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 0.1 MHz) | MJF127 MJF122 | C _{ob} | _ _ | 300 200 | pF |

^{3.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.

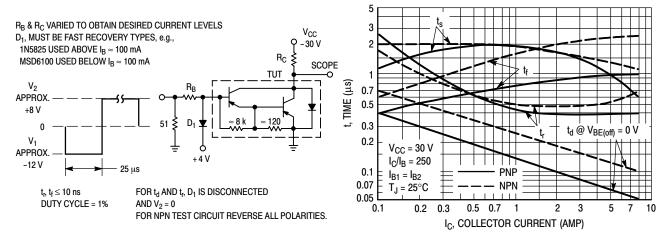


Figure 1. Switching Times Test Circuit

Figure 2. Typical Switching Times

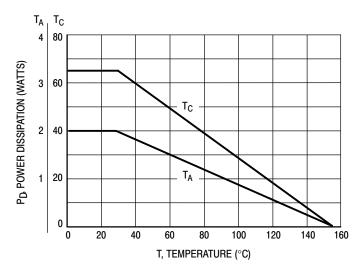


Figure 3. Maximum Power Derating

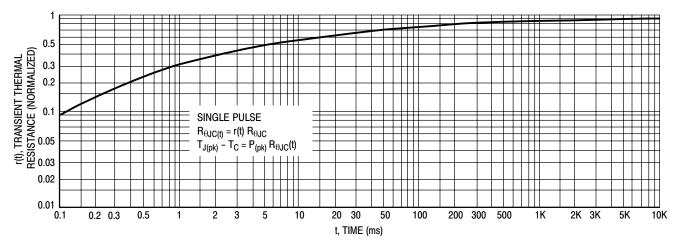


Figure 4. Thermal Response

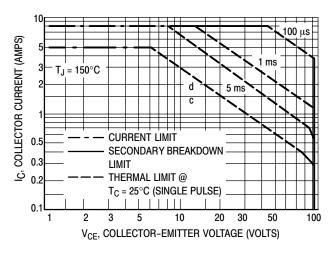
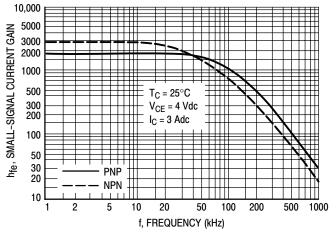


Figure 5. Maximum Forward Bias Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^{\circ}C$; T_C is variable depending on conditions. Secondary breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} < 150^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by secondary breakdown.

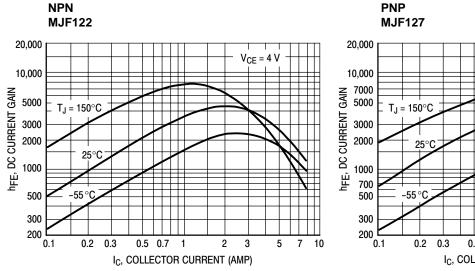
300



200 T_J = 25°C T_{Ob} T_J = 25°C T_D = 20°C T_D = 2

Figure 6. Typical Small-Signal Current Gain

Figure 7. Typical Capacitance



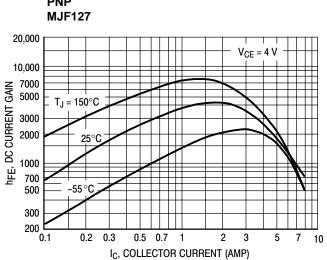
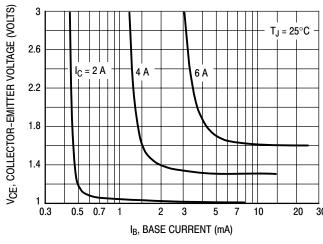


Figure 8. Typical DC Current Gain



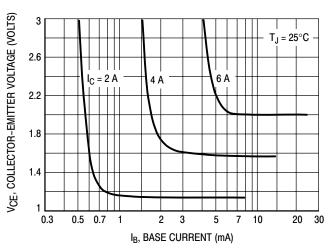


Figure 9. Typical Collector Saturation Region

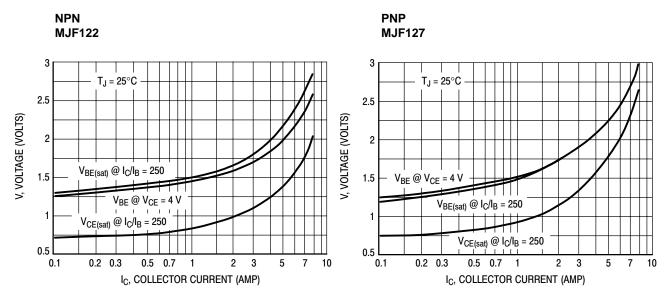


Figure 10. Typical "On" Voltages

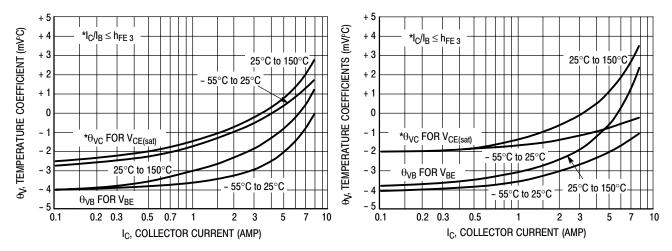


Figure 11. Typical Temperature Coefficients

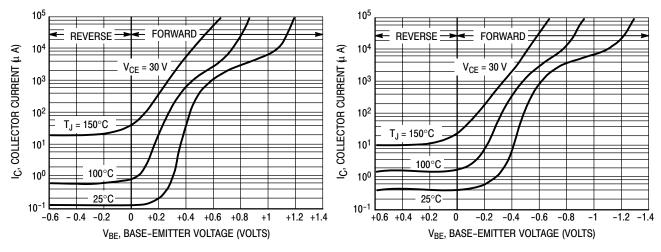


Figure 12. Typical Collector Cut-Off Region

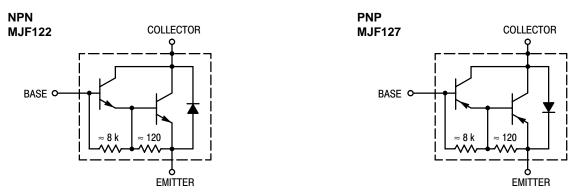


Figure 13. Darlington Schematic

TEST CONDITIONS FOR ISOLATION TESTS*

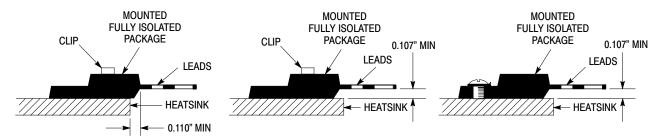


Figure 14. Clip Mounting Position for Isolation Test Number 1

Figure 15. Clip Mounting Position for Isolation Test Number 2

Figure 16. Screw Mounting Position for Isolation Test Number 3

*Measurement made between leads and heatsink with all leads shorted together

MOUNTING INFORMATION

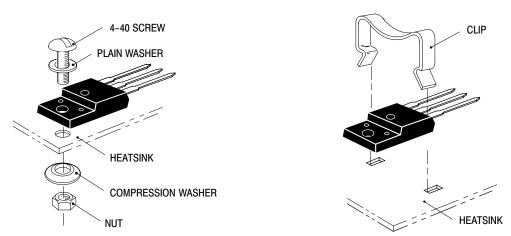


Figure 17. Typical Mounting Techniques*

Laboratory tests on a limited number of samples indicate, when using the screw and compression washer mounting technique, a screw torque of 6 to 8 in · lbs is sufficient to provide maximum power dissipation capability. The compression washer helps to maintain a constant pressure on the package over time and during large temperature excursions.

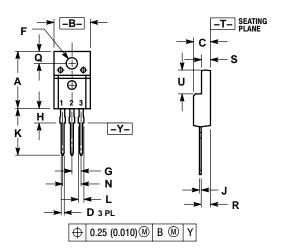
Destructive laboratory tests show that using a hex head 4–40 screw, without washers, and applying a torque in excess of 20 in · lbs will cause the plastic to crack around the mounting hole, resulting in a loss of isolation capability.

Additional tests on slotted 4–40 screws indicate that the screw slot fails between 15 to 20 in · lbs without adversely affecting the package. However, in order to positively ensure the package integrity of the fully isolated device, ON Semiconductor does not recommend exceeding 10 in · lbs of mounting torque under any mounting conditions.

^{**} For more information about mounting power semiconductors see Application Note AN1040.

PACKAGE DIMENSIONS

TO-220 CASE 221D-03 **ISSUE G**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH
 3. 221D-01 THRU 221D-02 OBSOLETE, NEW STANDARD 221D-03.

| | INCHES | | MILLIN | IETERS | |
|-----|-----------|-------|--------|----------|--|
| DIM | MIN | MAX | MIN | MAX | |
| Α | 0.625 | 0.635 | 15.88 | 16.12 | |
| В | 0.408 | 0.418 | 10.37 | 10.63 | |
| С | 0.180 | 0.190 | 4.57 | 4.83 | |
| D | 0.026 | 0.031 | 0.65 | 0.78 | |
| F | 0.116 | 0.119 | 2.95 | 3.02 | |
| G | 0.100 | BSC | 2.54 | BSC | |
| Н | 0.125 | 0.135 | 3.18 | 3.43 | |
| J | 0.018 | 0.025 | 0.45 | 0.63 | |
| K | 0.530 | 0.540 | 13.47 | 13.73 | |
| L | 0.048 | 0.053 | 1.23 | 1.36 | |
| N | 0.200 BSC | | 5.08 | 5.08 BSC | |
| Q | 0.124 | 0.128 | 3.15 | 3.25 | |
| R | 0.099 | 0.103 | 2.51 | 2.62 | |
| S | 0.101 | 0.113 | 2.57 | 2.87 | |
| U | 0.238 | 0.258 | 6.06 | 6.56 | |

STYLE 2:
PIN 1. BASE
2. COLLECTOR
3. EMITTER

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